IN THE ABSTRACT OF THE DISCLOSURE:

Please amend the abstract of the disclosure as follows:

ABSTRACT OF THE DISCLOSURE

~~The invention realizes, in~~ In a semiconductor device including n-channel field-effect transistors and p-channel field-effect transistors, in which ~~a~~ the channel direction is parallel to a ~~<100>~~ axis, a semiconductor device ~~having~~ in provided which has excellent drain current characteristics ~~of~~ at both n-channel field-effect transistors and p-channel field-effect transistors. In a semiconductor device including n-channel field-effect transistors N1 and N2 and p-channel field-effect transistors P1 and P2, a stress control film ~~209~~ that covers the gate electrodes of the n-channel and p-channel field-effect transistors from upper surfaces thereof is not formed, or is made thin, above shallow trench isolations adjacent to active regions formed by the p-channel field-effect transistors P1 and P2, in a case where the stress control film ~~209~~ is a tensile film stress. Thus, improvement of the drain currents of both the n-channel and p-channel transistors can be expected. For this reason, it is possible to improve overall characteristics.